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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-80CPU02-N3</u>

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Datasheet of VS-80CPU02-N3 - DIODE ARRAY GP 200V 40A TO247AC Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



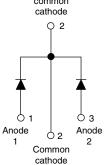
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Vishay Semiconductors

Ultrafast Rectifier, 2 x 40 A FRED Pt®







Base

PRODUCT SUMMARY						
Package	TO-247AC					
I _{F(AV)}	2 x 40 A					
V _R	200 V					
V _F at I _F	0.8 V					
t _{rr} typ.	34 ns					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- · Ultrafast recovery time
- · Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





HALOGEN FREE

DESCRIPTIONS / APPLICATIONS

VS-80CPU02... series are the state of the art ultrafast recovery rectifiers designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of welding, SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Repetitive peak reverse voltage	V_{RRM}		200	V			
Average rectified forward current total device	I _{F(AV)}	T _C = 145 °C	40				
			80	Α			
Non-repetitive peak surge current per leg	I _{FSM}	T _J = 25 °C	330				
Operating junction and storage temperatures	T_J , T_{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	OL TEST CONDITIONS MIN. TYP. M.						
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-			
Forward voltage		I _F = 40 A	-	0.94	1.02			
	V _F	I _F = 40 A, T _J = 150 °C	-	0.80	0.90	V		
		I _F = 80 A	-	1.07	1.20			
		I _F = 80 A, T _J = 150 °C	-	0.97	1.08			
Develope legica de autorit	_	$V_R = V_R$ rated	-	-	5			
Reverse leakage current	I _R	T _J = 150 °C, V _R = V _R rated	-	-	500	μΑ		
Junction capacitance	C _T	V _R = 200 V	-	120	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	3.5	-	nH		

Revision: 08-Jul-15 Document Number: 93457



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST C	ONDITIONS	MIN.	TYP.	MAX.	UNITS	
		I _F = 1.0 A, dI _F /dt =	I _F = 1.0 A, dI _F /dt = 100 A/μs, V _R = 30 V		34	-		
Reverse recovery time	t _{rr}	T _J = 25 °C	$I_F = 40 \text{ A}$ $dI_F/dt = -200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	33	-	ns - A	
		T _J = 125 °C		-	54	-		
Dools recovery ourrent		T _J = 25 °C		-	3.4	-		
Peak recovery current	I _{RRM}	T _J = 125 °C		-	8	-		
Reverse recovery charge	0	T _J = 25 °C		-	56	-	»C	
	Q _{rr}	T _J = 125 °C		-	216	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction to case per leg	R _{thJC}		-	0.46	0.70			
Thermal resistance, junction to ambient per leg	R _{thJA}	JA Typical socket mount		-	40	°C/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.3	-			
Weight			-	6.0	-	g		
vveigni			-	0.21	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-247AC	80CPU02					

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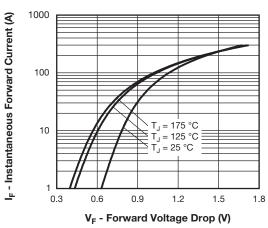


Fig. 1 - Typical Forward Voltage Drop Characteristics

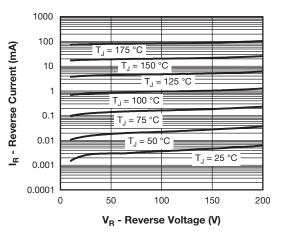


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

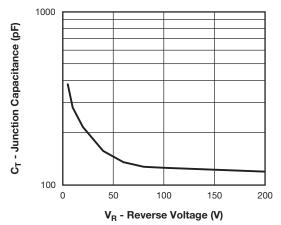


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

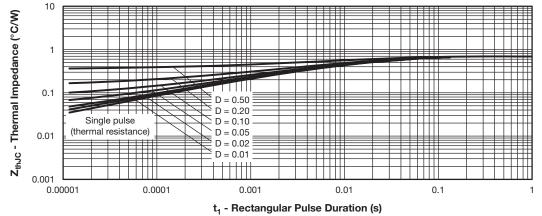


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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1000

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180

170

160

150

140

130

120

110

Allowable Case Temperature (°C)

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Square wave (D = 0.50) Rated V_R applied

See note (1)

10

DC

60

I_{F(AV)} - Average Forward Current (A)

Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

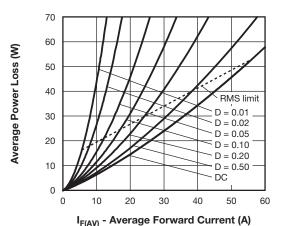


Fig. 6 - Forward Power Loss Characteristics

80 70 60 $I_F = 40 \text{ A}, T_J = 125 ^{\circ}\text{C}$ 30 $I_F = 40 \text{ A}, T_J = 25 ^{\circ}\text{C}$

Average values

10

100

 $\label{eq:dlf} dl_{\text{F}}/dt \, \text{(A/μs)}$ Fig. 7 - Typical Reverse Recovery Time vs. dl_{F}/dt

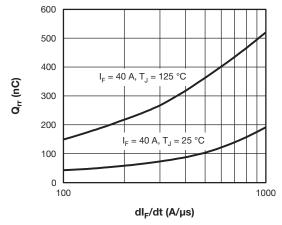


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} \ \ \text{Formula used:} \ T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \ \text{at} \ (I_{F(AV)}/D) \ (\text{see fig. 6}); \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \ (1 - D); \ I_R \ \text{at} \ V_{R1} = \text{Rated} \ V_R \\ \end{array}$

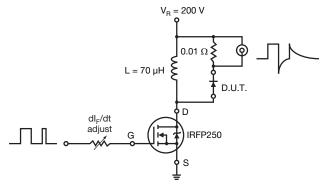


Fig. 9 - Reverse Recovery Parameter Test Circuit

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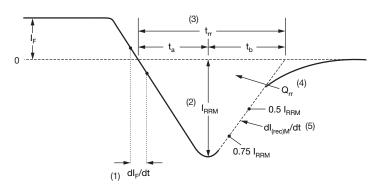
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- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

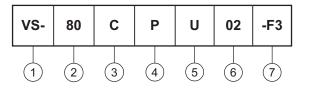
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- Current rating (80 = 80 A)
- Circuit configuration:

C = common cathode

P = TO-247AC

U = ultrafast rectifier

Voltage rating (02 = 200 V)

Environmental digit:

-F3 = RoHS-compliant and totally lead (Pb)-free

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-80CPU02-F3	25	500	Antistatic plastic tube				
VS-80CPU02-N3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95542</u>					
Part marking <u>www.vishay.com/doc?95007</u>					

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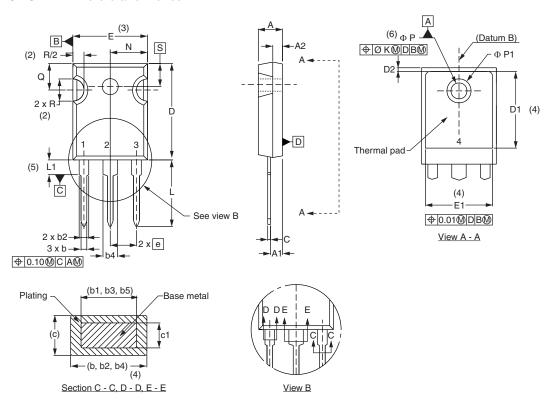


Outline Dimensions

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TO-247 - 50 mils L/F

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215	BSC	
ØK	0.254		0.0)10	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62	BSC	0.3		
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217	'BSC	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q

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